BLC9G20XS-160AV

Power LDMOS transistor

AMPLEON

Rev. 3 — 24 May 2017

Product data sheet

1. Product profile

1.1 General description

160 W LDMOS packaged asymmetric Doherty power transistor for base station applications at frequencies from 1805 MHz to 1990 MHz.

Table 1. Typical performance

Typical RF performance at T_{case} = 25 °C in an asymmetrical Doherty demo test circuit. V_{DS} = 30 V; I_{Dq} = 300 mA (main); $V_{GS(amp)peak}$ = 0.7 V, unless otherwise specified.

Test signal	f	V _{DS}	P _{L(AV)}	G _p	η_D	ACPR
	(MHz)	(V)	(W)	(dB)	(%)	(dBc)
1-carrier W-CDMA	1805 to 1880	30	28	16.6	47	-30 ^[1]

^[1] Test signal: 3GPP test model 1; 64 DPCH; PAR = 7.2 dB at 0.01% probability on CCDF per carrier.

1.2 Features and benefits

- Excellent ruggedness
- High-efficiency
- Low thermal resistance providing excellent thermal stability
- Designed for broadband operation (1805 MHz to 1990 MHz)
- Asymmetric design to achieve optimum efficiency across the band
- Lower output capacitance for improved performance in Doherty applications
- Designed for low memory effects providing excellent digital pre-distortion capability
- Internally matched for ease of use
- Integrated ESD protection
- Compliant to Directive 2002/95/EC, regarding Restriction of Hazardous Substances (RoHS)

1.3 Applications

 RF power amplifiers for base stations and multi carrier applications in the 1805 MHz to 1990 MHz frequency range

2. Pinning information

Table 2. Pinning

Pin	Description		Simplified outline	Graphic symbol
1	drain1 (main)			
2	drain2 (peak)		5 1 2 6	1, 5
3	gate1 (main)			3_
4	gate2 (peak)		7	7
5	video decoupling (main)			47
6	video decoupling (peak)		3 4	2, 6
7	source	[1]		aaa-007731

^[1] Connected to flange.

3. Ordering information

Table 3. Ordering information

Type number	Packag	Package					
	Name	Description	Version				
BLC9G20XS-160AV	-	air cavity plastic earless flanged package; 6 leads	SOT1275-1				

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage		-	65	V
V _{GS(amp)main}	main amplifier gate-source voltage		-5	+13	V
V _{GS(amp)peak}	peak amplifier gate-source voltage		-5	+13	V
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature	[1]	-	225	°C

^[1] Continuous use at maximum temperature will affect the reliability, for details refer to the online MTF calculator.

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Тур	Unit
R _{th(j-c)}	thermal resistance from junction	V_{DS} = 30 V; I_{Dq} = 300 mA (main);		
	to case	V _{GS(amp)peak} = 0.5 V; T _{case} = 80 °C		
		P _L = 44.5 dBm	0.30	K/W
		P _L = 46.5 dBm	0.22	K/W

6. Characteristics

Table 6. DC characteristics

 T_i = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Main dev	rice			1	1	
V _{(BR)DSS}	drain-source breakdown voltage	$V_{GS} = 0 \text{ V}; I_D = 0.6 \text{ mA}$	65	-	-	V
V _{GS(th)}	gate-source threshold voltage	V _{DS} = 10 V; I _D = 60 mA	1.5	2	2.5	V
V_{GSq}	gate-source quiescent voltage	V _{DS} = 30 V; I _D = 300 mA	1.65	2.2	2.75	V
I _{DSS}	drain leakage current	V _{GS} = 0 V; V _{DS} = 32 V	-	-	1.4	μΑ
I _{DSX}	drain cut-off current	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $V_{DS} = 10 \text{ V}$	-	12.2	-	Α
I _{GSS}	gate leakage current	V _{GS} = 11 V; V _{DS} = 0 V	-	-	140	nA
9 _{fs}	forward transconductance	V _{DS} = 10 V; I _D = 3.0 A	-	4.56	-	S
R _{DS(on)}	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $I_D = 2.1 \text{ A}$	-	237	385	mΩ
Peak dev	rice			1		
V _{(BR)DSS}	drain-source breakdown voltage	$V_{GS} = 0 \text{ V}; I_D = 1.1 \text{ mA}$	65	-	-	V
V _{GS(th)}	gate-source threshold voltage	V _{DS} = 10 V; I _D = 110 mA	1.5	2	2.5	V
V_{GSq}	gate-source quiescent voltage	V _{DS} = 30 V; I _D = 660 mA	1.6	2.1	2.6	V
I _{DSS}	drain leakage current	V _{GS} = 0 V; V _{DS} = 32 V	-	-	1.4	μΑ
I _{DSX}	drain cut-off current	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $V_{DS} = 10 \text{ V}$	-	21.7	-	Α
I _{GSS}	gate leakage current	V _{GS} = 11 V; V _{DS} = 0 V	-	-	140	nA
9 _{fs}	forward transconductance	V _{DS} = 10 V; I _D = 5.5 A	-	8.16	-	S
R _{DS(on)}	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $I_D = 3.85 \text{ A}$	-	129	214	mΩ

Table 7. RF characteristics

Test signal: 1-carrier W-CDMA; PAR = 7.2 dB at 0.01 % probability on the CCDF; 3GPP test model 1; 1 to 64 DPCH; RF performance at V_{DS} = 30 V; I_{Dq} = 300 mA (main); $V_{GS(amp)peak}$ = 0.5 V; T_{case} = 25 °C; unless otherwise specified; in an asymmetrical Doherty production test circuit at frequencies from 1805 MHz to 1880 MHz.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Gp	power gain	P _{L(AV)} = 28 W	15.2	16.4	-	dB
RLin	input return loss	P _{L(AV)} = 28 W	-	-10	-5	dB
η_{D}	drain efficiency	P _{L(AV)} = 28 W	41.4	46	-	%
ACPR	adjacent channel power ratio	P _{L(AV)} = 28 W	-	-30	-23	dBc

Table 8. RF characteristics

Test signal: pulsed CW; t_p = 100 μ s; δ = 10 %; RF performance at V_{DS} = 30 V; I_{Dq} = 300 mA (main); $V_{GS(amp)peak}$ = 0.5 V; T_{case} = 25 °C; unless otherwise specified; in an asymmetrical Doherty production test circuit at frequencies from 1805 MHz to 1880 MHz.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$P_{L(M)}$	peak output power		160	190	-	W

7. Test information

7.1 Ruggedness in Doherty operation

The BLC9G20XS-160AV is capable of withstanding a load mismatch corresponding to a VSWR = 10 : 1 through all phases under the following conditions: V_{DS} = 30 V; I_{Dq} = 300 mA (main); $V_{GS(amp)peak}$ = 0.5 V; P_L = 135 W (CW); f = 1805 MHz.

7.2 Impedance information

Table 9. Typical impedance of main device

Measured load-pull data of main device; I_{Dq} = 360 mA (main); V_{DS} = 30 V.

f	Z _S [1]	Z _L [1]	P _L [2]	η _D [2]	G _p [2]					
(MHz)	(Ω)	(Ω)	(W)	(%)	(dB)					
Maximum	Maximum power load									
1805	2.20 - j8.08	2.85 - j5.54	49.68	61.09	16.57					
1843	3.40 – j8.84	2.85 - j5.54	49.56	60.83	16.55					
1880	3.67 – j9.16	2.69 - j5.13	49.38	59.43	16.48					
Maximum	drain efficiency loa	d								
1805	2.20 - j8.08	5.06 – j4.14	48.40	69.34	18.42					
1843	3.40 – j8.84	4.84 – j2.59	47.52	68.53	18.61					
1880	3.67 – j9.16	5.00 - j3.33	47.79	67.95	18.99					

^[1] Z_S and Z_L defined in Figure 1.

Table 10. Typical impedance of peak device

Measured load-pull data of peak device; I_{Dq} = 660 mA (peak); V_{DS} = 30 V.

f	Z _S [1]	Z _L [1]	P _L [2]	η _D [2]	G _p [2]					
(MHz)	(Ω)	(Ω)	(W)	(%)	(dB)					
Maximum pov	Maximum power load									
1805	1.76 – j7.22	2.61 – j6.60	51.62	54.98	15.72					
1843	3.07 – j7.53	2.61 – j6.60	51.43	54.14	15.60					
1880	3.44 – j8.15	2.61 – j6.60	51.29	53.36	15.75					
Maximum dra	in efficiency load									
1805	1.76 – j7.22	4.65 – j3.75	50.09	66.75	18.39					
1843	3.07 – j7.53	3.91 – j3.12	49.50	65.85	18.49					
1880	3.44 – j8.15	3.94 – j3.76	49.80	64.54	18.55					

^[1] Z_S and Z_L defined in Figure 1.

^[2] at 3 dB gain compression.

^[2] at 3 dB gain compression.

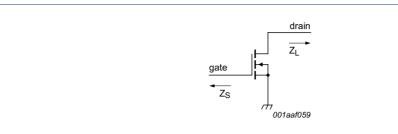


Fig 1. Definition of transistor impedance

7.3 Recommended impedances for Doherty design

Table 11. Typical impedance of main device at 1:1 load

Measured load-pull data of main device; I_{Dq} = 300 mA (main); V_{DS} = 30 V.

f	Z _S [1]	Z _L [1]	P _L [2]	η _D [3]	G _p [3]
(MHz)	(Ω)	(Ω)	(dBm)	(%)	(dB)
1805	2.20 – j8.08	1.83 – j4.0	49.09	55.81	19.68
1843	3.40 – j8.84	1.80 – j3.7	49.15	56.21	19.40
1880	3.67 – j9.16	1.77 – j3.4	49.09	55.86	19.41

- [1] Z_S and Z_L defined in Figure 1.
- [2] at 3 dB gain compression.
- [3] at $P_{L(AV)} = 44.5 \text{ dBm}$.

Table 12. Typical impedance of main device at 1 : 2.7 load

Measured load-pull data of main device; I_{Dq} = 300 mA (main); V_{DS} = 30 V.

f	Z _S [1]	Z _L [1]	P _L [2]	η _D [3]	G _p [3]
(MHz)	(Ω)	(Ω)	(dBm)	(%)	(dB)
1805	2.20 – j8.08	4.30 – j2.46	47.11	64.24	22.15
1843	3.40 – j8.84	4.31 – j2.29	46.77	62.36	22.36
1880	3.67 – j9.16	4.31 – j2.12	46.61	60.79	22.70

- [1] Z_S and Z_L defined in Figure 1.
- [2] at 3 dB gain compression.
- [3] at $P_{L(AV)} = 44.5 \text{ dBm}$.

7.4 Test circuit

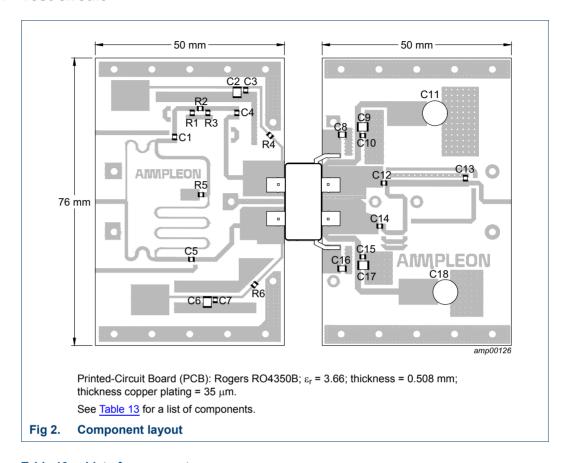


Table 13. List of components

See Figure 2 for component layout.

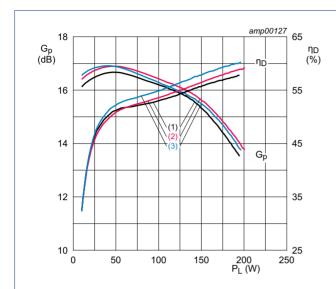
Component	Description	Value	Remarks
C1, C3, C4, C5, C7, C10, C14, C15	multilayer ceramic chip capacitor	36 pF [1]	
C2, C6, C8, C9, C16, C17	multilayer ceramic chip capacitor	10 μF, 50 V	
C11, C18	electrolytic capacitor	1000 μF, 63 V	
C12	multilayer ceramic chip capacitor	6.8 pF [1]	
C13	multilayer ceramic chip capacitor	0.2 pF [1]	
R1, R3	resistor	910 Ω	SMD 0805
R2, R4, R6	resistor	5.1 Ω	SMD 0805
R5	resistor	50 Ω	SMD 0805

^[1] American Technical Ceramics type 600F or capacitor of same quality.

^[2] Murata or capacitor of same quality.

7.5 Graphical data

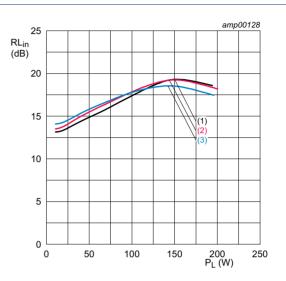
7.5.1 Pulsed CW



 V_{DS} = 30 V; I_{Dq} = 300 mA (main device); $V_{GS(amp)peak}$ = 0.5 V.

- (1) f = 1805 MHz
- (2) f = 1842.5 MHz
- (3) f = 1880 MHz

Fig 3. Power gain and drain efficiency as function of output power; typical values

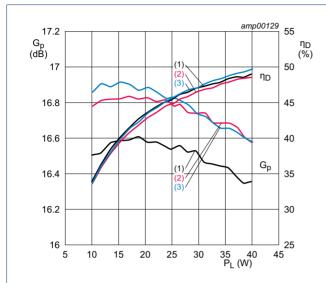


 V_{DS} = 30 V; I_{Dq} = 300 mA (main device); $V_{GS(amp)peak}$ = 0.5 V.

- (1) f = 1805 MHz
- (2) f = 1842.5 MHz
- (3) f = 1880 MHz

Fig 4. Input return loss as a function of output power; typical values

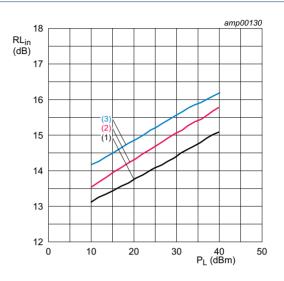
7.5.2 1-Carrier W-CDMA



 V_{DS} = 30 V; I_{Dq} = 300 mA (main device); $V_{GS(amp)peak}$ = 0.5 V.

- (1) f = 1805 MHz
- (2) f = 1842.5 MHz
- (3) f = 1880 MHz

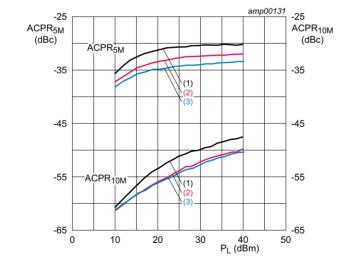
Fig 5. Power gain and drain efficiency as function of output power; typical values



 V_{DS} = 30 V; I_{Dq} = 300 mA (main device); $V_{GS(amp)peak}$ = 0.5 V.

- (1) f = 1805 MHz
- (2) f = 1842.5 MHz
- (3) f = 1880 MHz

Fig 6. Input return loss as a function of output power; typical values

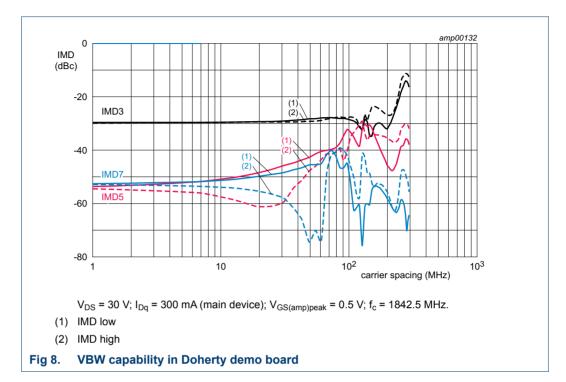


 V_{DS} = 30 V; I_{Dq} = 300 mA (main device); $V_{GS(amp)peak}$ = 0.5 V.

- (1) f = 1805 MHz
- (2) f = 1842.5 MHz
- (3) f = 1880 MHz

Fig 7. Adjacent channel power ratio (5 MHz) and adjacent channel power ratio (10 MHz) as function of output power; typical values

7.5.3 2-Tone VBW



8. Package outline

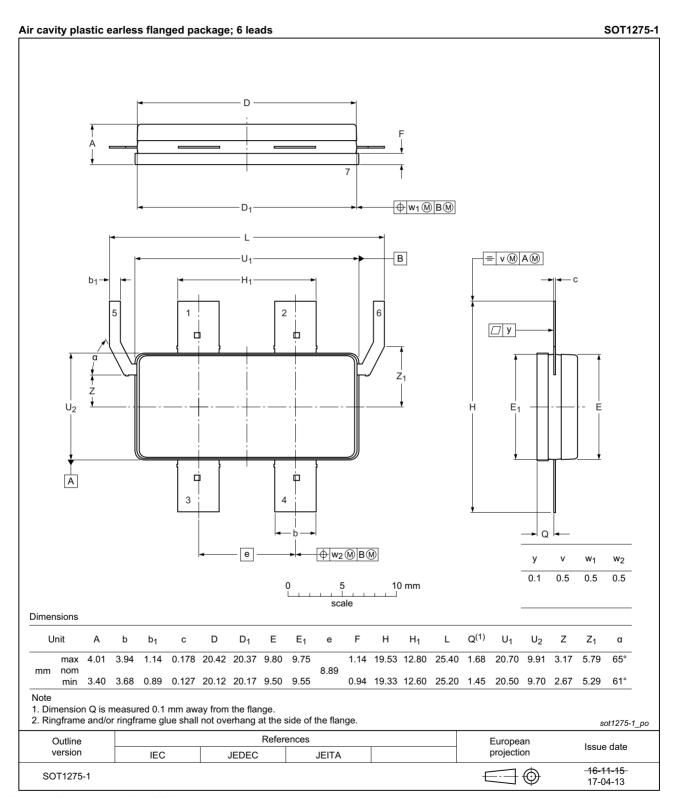


Fig 9. Package outline SOT1275-1

9. Handling information

CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the ANSI/ESD S20.20, IEC/ST 61340-5, JESD625-A or equivalent standards.

Table 14. ESD sensitivity

ESD model	Class
Charged Device Model (CDM); According to ANSI/ESDA/JEDEC standard JS-002	C2A [1]
Human Body Model (HBM); According to ANSI/ESDA/JEDEC standard JS-001	2 [2]

^[1] CDM classification C2A is granted to any part that passes after exposure to an ESD pulse of 500 V, but fails after exposure to an ESD pulse of 750 V.

10. Abbreviations

Table 15. Abbreviations

Acronym	Description
3GPP	3rd Generation Partnership Project
CCDF	Complementary Cumulative Distribution Function
CW	Continuous Wave
DPCH	Dedicated Physical CHannel
ESD	ElectroStatic Discharge
LDMOS	Laterally Diffused Metal-Oxide Semiconductor
MTF	Median Time to Failure
PAR	Peak-to-Average Ratio
SMD	Surface Mounted Device
VBW	Video Bandwidth
W-CDMA	Wideband Code Division Multiple Access

11. Revision history

Table 16. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BLC9G20XS-160AV v.3	20170524	Product data sheet	-	BLC9G20XS-160AV v.2
Modifications:	<u>Table 2 on page 2</u> : change simplified outline			
	<u>Table 3 on page 2</u> : change version to SOT1275-1			
	Figure 9 on page 10: change package outline drawing to SOT1275-1			
BLC9G20XS-160AV v.2	20161220	Product data sheet	-	BLC9G20XS-160AV v.1
BLC9G20XS-160AV v.1	20161019	Product data sheet	-	-

^[2] HBM classification 2 is granted to any part that passes after exposure to an ESD pulse of 2000 V, but fails after exposure to an ESD pulse of 4000 V.

12. Legal information

12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Power LDMOS transistor

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BLC9G20XS-160AV

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